MITSUBISHI ICs (TV)

PRELIMINARY

Notice ; This is not a final specification. Some parametric limits are subject to change. M61130FP

DESCRIPTION

The M61130FP is a semiconductor integrated circuit consisting of Tuner signal processing for NTSC color TV sets and VCRs. The circuit includes Mixer circuit in Tuning system, Oscillator circuit, PLL frequency synthesizer and VIF/SIF, which permits a smaller tuner system.

FEATURES

VIF/SIF Inter carrier type for NTSC Coil-less VCO Adjustment free AFT High-speed IF AGC
PLL Low phase noise and High-speed lock-up Built-in band switch driver (4 port) I²C bus control Available for both XO and external reference
Mixer/Oscillator Built in LI8V concillator and mixer

Built-in U&V oscillator and mixer Built-in UV band switch

APPLICATION

TV, VTR

RECOMMENDED OPERATING CONDITIONS

Supply voltage range......4.75 to 5.25V Recommended supply voltage.....5.0V





PRELIMINARY

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M61130FP

TUNER SINGLE CHIP





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TUNER SINGLE CHIP

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise noted)

Symbol	Parameter	Raitings	Unit
Vcc	Supply Voltage	6.0	V
Pd	Power Dissipation	658	mW
Topr	Operating temperature	-20 to +75	О°
Tstg	Storage temperature	-40 to +150	°C

TYPICAL CHARACTERISTICS



ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise noted)

Symbol	Parameter	Measure	Test conditions		Limits		Unit
Symbol	Falameter	Point	Test conditions	Min	Тур	Max	Offic
IF Icc	IF Vcc current	28		-	70	84	mA
MO Icc	M/O Vcc current	36		-	21	25	mA
Log Icc	Logic Vcc current	32	Port output off	-	14	20	mA
Log Icc(U)	Logic Vcc current(UHF)	32	lo _{BS} =-22mA	-	40	46	mA
Log Icc(V)	Logic Vcc current(VHF)	32	lo _{bs} =-25mA	-	43	50	mA
Log Icc(F)	Logic Vcc current(FM(32	lo _{BS} =-15mA	-	32	38	mA
Ibavideo	Video out bias current	16		1.4	1.9	2.4	mA
IbaAudio	Audio out bias current	21		1.0	1.3	1.6	mA
IbaQIF	4.5MHz QIF out bias current	20		0.9	1.2	1.5	mA
Vreg	Regulator voltage	12		2.65	2.8	2.95	V
fxosc	X'tal frequency	31	PLL function range	3.0	4.0	4.8	MHz
frefin	Ref. signal frequency	31	PLL function range	3.0	4.0	5.0	MHz
Vifrefin	Ref. signal input level	31		50	-	600	mVp-p



PRELIMINARY

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TUNER SINGLE CHIP

ELECTRICA CHARACTERISTICS (cont.)

M/O

Symbol	Parameter	Measure	Test conditions		Limits		
Symbol	Farameter	Point	Test conditions	Min Typ Max		Unit	
Band VHF	Mixer		RL=75				
GpVHF1	Conversion gain1	26,44	fRF=57.5MHz	16	19	22	dB
GpVHF2	Conversion gain2	26,44	fRF=357.5MHz	16	19	22	dB
NFVHF	Noise figure	26,44	fRf=57.5~357.5MHz		11		dB
CM1VHF	1% cross modulation1	26,44	fRF=55.25MHz	90	Min Typ Max 16 19 22 16 19 22 11 11 11		dBµV
CM2VHF			fRF=361.25MHz	90			dBµV
Band UHF	l Mixer		RL=75				
GpUHF1	Conversion gain1	26,45,46	fRF=369.5MHz	26	29	32	dB
GpUHF2	Conversion gain2	26,45,46	fRF=803.5MHz	26	29	32	dB
NFUHF	Noise figure	26,45,46	fRF=369.5~803.5MHz		10		dB
CM1UHF	1% cross modulation1	26,45,46	fRF=367.25MHz	80			dBµV
CM2UHF	1% cross modulation2	26,45,46	fRF=801.25MHz	80			dBµV
Band VHF	l Oscillator						
foVHF	Operation range	26		101		407	MHz
fosc(v)	Supply voltage drift	26	Vcc=5%		100		KHz
foV(t)	SW ON drift	26	3sec~3min after SW ON		200		KHz
Band UHF	l Oscillator						
foUHF	Operation range	26		413		847	MHz
fosc(U)	Supply voltage drift	26	Vcc=5%		100		KHz
foU(t)	SW ON drift	26	3sec~3min after SW ON		200		KHz

PLL

Symbol	Parameter	Measure	Test conditions		Limits		Unit
Symbol	Parameter	Point	Test conditions	Min Typ Max		Unit	
nput term	inals						
ViH	Hi input voltage	33,34		3.0	-	Vcc +0.3	V
ViL	Lo input voltage	33,34		-	-	1.5	V
liH1	Hi input current	33,34	Vcc=5.5V,Vi=4.0V	-	-	10	μA
liL1	Lo input current	33,34	Vcc=5.5V,Vi=0.4V	-	-	-10	μA
SDA outpu	ut						
VsiL	Lo output voltage	34	Vcc=5.5V,Io=3mA	-	-	0.4	V
lsLK	Leakage current	34	Vcc=5.5V,Vo=5.5V	-	-2	-10	μA
ADS input	1						
liH2	Hi input current	35	Vcc=5.5V,Vi=5.0V	-	-	10	μA
liL2	Lo input current	35	Vcc=5.5V,Vi=1.5V	-	-15	-30	μA
Band outp	but						
VoBS1	Output voltage1	39,40	Vcc=5.0V,Io=-25mA PVHFL,PVHFH	4.6	4.8	-	V
VoBS2	Output voltage2	47	Vcc=5.0V,Io=-22mA,PUHF	4.6	4.8	-	V
VoBS3	Output voltage3	38	Vcc=5.0V,Io=-5mA,PFMST	4.6	4.8	-	V
loBSLK	Output voltage3 3 Leakage current 38,3 4 4		Vcc=5.5V,Output is OFF		-	10	μA
Charge pu	ımp						
lcpH	Hi output current	7	Vcc=5.5V,Vo=2.5V,CP=1	160	270	360	μA
lcpL	Lo output current	7	Vcc=5.5V,Vo=2.5V,CP=0	50	70	110	μA
lcpLK	Leakage current	7	Vcc=5.5V,Vo=5.5V,T2,T1=0	-	-	50	nA



PRELIMINARY

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TUNER SINGLE CHIP

ELECTRICA CHARACTERISTICS (cont.)

VIF/SIF

Symbol	Parameter	Measure	Test conditions		Limits		Unit
Symbol	Farameter	Point	Test conditions	Min	Тур	Max	Unit
VoDET	Video output level	16	IF 77.78%, 15.7KHz AM, 90dBµ	1.1	1.3	1.5	Vp-p
Vsync	Sync tip voltage	13		1.1	1.3	1.5	V
VSN	Video S/N	13	with 6MHz LPF, 90dBµV	48	50	-	dB
BW	Video out freq. response	16	loss 6MHz	-	3	5	dB
VINMIN	Input sensitivity	13,23,24	-3dB down point		45	49	dBµV
VINMAX	Max. IF input	13,23,24	+3dB up point	101	105	-	dBµV
GR	AGC range	-		54	60	-	dB
V10	IF AGC voltage	10		2.7	2.9	3.1	V
V10L	IF AGC min. voltage	10	110dBµV	1.9	2.1	2.3	V
CL-U	Capture range U	23,24	45.75MHz, 90dBµV	1.5	2.5	-	MHz
CL-L	Capture range L	23,24	45.75MHz, 90dBµV	1.5	1.9	-	MHz
D/G	D/G	13		-	3	5	%
D/P	D/P	13		-	3	5	deg
RINV	VIF input impedance	23,24	DC	-	2k	-	
CINV	VIF input capacitance	23,24	40MHz	-	5	-	pF
foC1	AFT Center freq. 45.75MHz	19,23,24	pin19 voltage = Vcc/2	-30	fo	+30	KHz
foC2	AFT Center freq. 58.75MHz	19,23,24	pin19 voltage = Vcc/2	-30	fo	+30	KHz
V19H	Hi output voltage	19	Vcc=5.0V	4.3	4.7	5.0	V
V19L	Lo output voltage	19		0	0.3	0.7	V
V19C	Center voltage	19	45.75MHz	2.3	2.5	2.7	V
μ	Sensitivity	19	360K //360K	10	24	36	mV/KHz
VRFH	RFAGC Hi output voltage	37	open	4.4	4.7	5.0	V
VRFLV	RFAGC Lo output voltage	37	open	0	0.3	0.6	V
RFDLY	RFAGC Delay point	23,24,37	@11pin 2V	87	90	93	dBµV
VoAF	Audio out level	23,24,37	4.5MHz±25kHz 1kHz	660	770	880	mVrms
VUAF		21		000	110	860	111111115
THDAF	Audio out THD	21	4.5MHz±25kHz 1kHz	-	0.2	0.9	%
AFSN	Audio out S/N	21	4.5MHz±25kHz 1kHz	54	57	-	dB
LIM	Limiting sensitivity	11,21		-	50	55	dBµV
AMR	AMR	21		50	55	-	dB
7		21					
VoQIF	QIF output	20		94	100	-	dBµV



PRELIMINARY

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CONTROL TABLE

VIF frequency select

	VIF frequency	20pin condition			
US	45.75 MHz	none			
JAPAN	58.75 MHz	pull down (1.5K)			

Ref input	
Ref in (31pin)	31pin condition
INT	none
EXT	pull down (2K)

BUS CONTROL

1)ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Measure	Test conditions		Limits		Unit
Symbol	Falametei	Point		Min	Тур	Max	Unit
fSCL	Clock frequency	33		0	100	400	KHz
tBUF	Bus free time	34		1.3	-	-	µsec
tHDSTA	Data hold time	34		0.6	-	-	µsec
tLOW	SCL LOW hold time	33		1.3	-	-	µsec
tHIGH	SCL HIGH hold time	33		0.6	-	-	µsec
tSUSTA	Set up time	33,34		0.6	-	-	µsec
tHDDAT	Data hold time	33,34		0	-	-	µsec
tSUDAT	Data set up time	33,34		100	-	-	nsec
tR	Rise time	33,34		-	-	300	nsec
tF	Fall time	33,34		-	-	300	nsec
tSUSTO	Set up time	33		0.6	-	-	µsec



2)Setting Data

The input information consisting of data of 2 or 4 bytes after chip address is received into I²C bus receiver. The definition of bus protocol admitted is shown as below.

Mode_1	STA	CA	DB1	DB2	CB1	CB2	STO
Mode_2	STA	CA	CB1	CB2	DB1	DB2	STO
Mode_3	STA	CA	DB1	DB2	STO		
Mode_4	STA	CA	CB1	CB2	STO		

STA : Start condition
STO : Stop condition
CA : Chip address
DB1 : Divider data byte 1
DB2 : Divider data byte 2
CB1 : Control data byte 1
CB2 : Band data byte 2

The information of 5 bytes required for circuit operational chip address, control data and band SW data of 2 bytes and divider data of 2 bytes. After the chip address input, 2 or 4 bytes can be received. Function bit is contained in the first and the third data byte to distinguish between divider and 'control data/band SW data', with "0" going ahead of divider data, and "1" going ahead of control data/band SW data'.

The timing of Writing data for bus protocol Mode is shown in the figure below. Divider data uses 15 bits and is read in at the rise of the eighth clock bit of the second byte divider data (D2).

Control data (CB) and band SW-data (BB) are each read in at the rise of their eighth clock bit.

Timin	ng Chart 2							
SDA		address	DB1	DB2	CB1	CB2		_
SCL				<u></u>				
			Read into late	ch Read into	latchRead	into latch —	_	



TUNER SINGLE CHIP

PRELIMINARY

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TUNER SINGLE CHIP

Write mode data format

While mode data format									
Byte	MSB							LSB	
Address Byte (CA)	1	1	0	0	0	MA1	MA0	R/W=0	Α
Divider Byte1 (DB1)	0	N14	N13	N12	N11	N10	N9	N8	Α
Divider Byte2 (DB2)	N7	N6	N5	N4	N3	N2	N1	N0	Α
Control Byte (CB1)	1	CP	T2	T1	TO	Rsa	Rsb	OS	Α
Band Byte (CB2)	RE	AFT	X	Х	PUHF	PFMST	PVHFH	PVHFL	Α

MA1,MA0 : Programmable Address Bit

Address input voltage applied to ADS [V]	MA1	MA0
0 to 0.1×Vcc	0	0
Always Valid	0	1
0.4×Vcc to 0.6×Vcc	1	0
0.9×Vcc to Vcc	1	1

N14 to N0 : How to set division ratio of the programmable divider

Division ratio N: N=N14(2^{14})+N13(2^{13})+ --- +N0(2^{0}) Range of division ratio N: N=1,024 to 32,767 Frequency of VCO fvco: fvco=fref × N

CP : Set up the charge pump current

CP	Charge pump current				
0	70µA				
1	270µA				

In the case of setting current 270 μ A, when PLL is locked, charge pump current is automatically switched to CP=O (70 μ A).

T2,T1,T0 : Set up for test mode

CP	T2	T1	T0	Charge pump	Test output	Test SW	Mode
0	0	0	Х	CP switched off	-	OFF	Normal mode
1	0	0	Х	CP switched on	-	OFF	Normal mode
Х	0	1	Х	High impedance	-	OFF	Test mode
0	1	1	0	Sink, CP current "Low"	-	OFF	Test mode
1	1	1	0	Sink, CP current "High"	-	OFF	Test mode
0	1	1	1	Source, CP current "Low"	-	OFF	Test mode
1	1	1	1	Source, CP current "High"	-	OFF	Test mode
0	1	0	0	High impedance	fREF	OFF	Test mode
1	1	0	Х	CP switched on	-	ON	Test mode
0	1	0	1	High impedance	f1/N	OFF	Test mode

Note : fREF and f1/N is available on pin PFMST

: Test SW is for the mix filter damping switch

Rsa,Rsb : Set up tuning step

Rsa	Rsb	Division ratio	tuning step frequency	
0	1	1/128	31.25KHz	
1	1	1/64	62.5KHz	
Х	0	1/80	50.0KHz	@4MHz X'tal

OS : Set up drive output

OS	Drive output	Mode
0	ON	Normal mode
1	OFF("L")level	Test mode



PRELIMINARY

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TUNER SINGLE CHIP

RE: Select of Reference frequency for automatic adjustment of VIF VCO free-running frequency.

KE	Reference frequency
0	3.58MHz
1	4.00MHz

AFT:Set up AFT mute

AFT	AFT mute voltage			
0	Low			
1	center			

PFMST, PUHF, PVHFL, PVHFH: PORT

FMST,PUHF,PVHFL,PVHF	Output
0	OFF
1	ON

PNP open collector output. When PUHF is "OFF", Mixer and Oscillator active VHF mode.

Read mode data format

Byte	MSB							LSB	
Address Byte	1	1	0	0	0	MA1	MA0	R/W=1	Α
Status Byte	POR	FL	ACPS	Х	Х	Х	Х	Х	Α

X: 0 or 1 Don't care

POR: Power on reset flag. Output is "1" at power-on

FL: Lock detector flag. Output is "1" at locked, output is "0" at unlocked.

ACPS: Automatic charge pump current flag. Output is "0" at charge pump current automatically switched mode , output is "1" at other mode.

Power on reset

The initial status are shown as below when supply voltage is turned on.

If supply voltage becomes less than about 3.0V, the initial status is set.

Byte	MSB							LSB
Divider Byte1 (DB1)	0	Х	Х	Х	Х	Х	Х	Х
Divider Byte2 (DB2)	Х	Х	Х	Х	Х	Х	Х	Х
Control Byte (CB1)	1	1	0	1	Х	1	1	1
Band Byte (CB2)	0	0	Х	Х	0	0	0	0

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TUNER SINGLE CHIP

APPLICATION EXAMPLE



PRELIMINARY

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TUNER SINGLE CHIP

DETAILED DIAGRAM OF PACKAGE OUTLINE





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